PROCEEDINGS OF SPIE

# *Extreme Ultraviolet (EUV) Lithography XII*

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*Editors*

**22–26 February 2021**
**Online Only, United States**

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ASML US, Inc. (United States)

*Published by*
SPIE

**Volume 11609**

Proceedings of SPIE 0277-786X, V. 11609

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Extreme Ultraviolet (EUV) Lithography XII, edited by Nelson M. Felix,
Anna Lio, Proc. of SPIE Vol. 11609, 1160901 · © 2021 SPIE
CCC code: 0277-786X/21/$21 · doi: 10.1117/12.2595815

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Please use the following format to cite material from these proceedings:
Author(s), "Title of Paper," in *Extreme Ultraviolet (EUV) Lithography XII*, edited by Nelson M. Felix, Anna Lio, Proceedings of SPIE Vol. 11609 (SPIE, Bellingham, WA, 2021) Seven-digit Article CID Number.

ISSN: 0277-786X
ISSN: 1996-756X (electronic)

ISBN: 9781510640511
ISBN: 9781510640528 (electronic)

Published by
**SPIE**
P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
SPIE.org
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